

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

PHONE: (215) 631-9840 FAX: (215) 631-9855

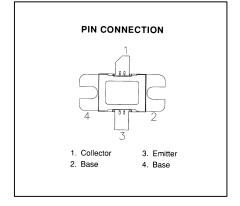
MS2472

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

Features

- DESIGNED FOR HIGH POWER PULSED IFF AND DME APPLICATIONS
- 600 W (typ.) IFF 1030 1090 MHz
- 550 W (min.) DME 1025 1150 MHz
- 1025 1150 MHz
- P_{OUT} = 550 WATTS
- G_P = 5.6 dB MINIMUM
- GOLD METALLIZATION
- INTERNAL INPUT/OUTPUT MATCHED
- COMMON BASE CONFIGURATION

.400 x .500 2LFL (M112) hermetically sealed



DESCRIPTION:

The MS2472 is a hermetically sealed, gold metallized, silicon NPN power transistor. The MS2472 is designed for applications requiring high peak power and low duty cycles such as IFF and DME. The MS2472 is internal input/output matched resulting in improved broadband performance and a low thermal resistance.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25° C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	65	V
V _{CES}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	3.5	V
Ic	Device Current	40	Α
P _{DISS}	Power Dissipation	1350	W
TJ	Junction Temperature	200	٥C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)} Ther	mal Resistance Junction-case	0.06	°C/W
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MS2472

ELECTRICAL SPECIFICATIONS (Tcase = 25°C) STATIC

Cumbal	Test Conditions			Value		
Symbol			Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 25 mA	I _E = 0 mA	65			V
BV _{CES}	I _C = 50 mA	V _E = 0 V	65			V
BV _{EBO}	I _C = 10 mA	$I_C = 0 \text{ mA}$	3.5			V
I _{CES}	V _{CE} = 50 V	I _E = 0 mA			35	mA
H _{FE}	V _{CE} = 5 V	$I_C = 0.25 A$	5		200	

DYNAMIC

Symbol	Symbol Test Conditions		Value		
Syllibol			Тур.	Max.	Unit
P _{out}	f = 1025 - 1150MHz P _{IN} = 150W V _{CE} = 50V	550			w
G _P	f = 1025 - 1150MHz P _{IN} = 150W V _{CE} = 50V	5.6			dB

Conditions: Pulse Width = 10 μ s Duty Cycle = 1%

IMPEDANCE DATA

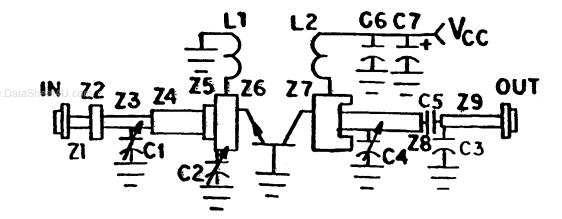
FREQ	$Z_IN(\Omega)$	$Z_{CL}\!(\Omega)$		
1025 MHz	2.50 + j2.7	1.33 - j1.7		
1090 MHz	2.60 + j1.6	1.33 - j1.9		
1150 MHz	1.90+ j0.7	1.33 - j2.1		

 $\begin{aligned} P_{\text{IN}} &= 150W \\ V_{\text{CC}} &= 50V \end{aligned}$



MS2472

TEST CIRCUIT



All Dimensions are in inches Unless Otherwise Specified

: 0.4 - 2.5pF Johanson Gigatrim

C2, C3, C4 : 0.6 - 4.5pF Johanson Gigatrim C5 : 82pF Chip Capacitor, .055 Sq.

C6 : Pair of 820pF Chip Capacitors, .11 Sq. : 1000µF Electrolytic C7

: Loop, #18 Tinned, .36 Wide x .27 Above Circuit

4 3/4 Turns, #24 Enameled, Close Wound. .075 I.D. L2

Z1 : 50Ω (.02 Wide) : .250 x .120

Z2

Z3 Z4 50Ω , .020 x .330; C1 Tapped .15 From Load

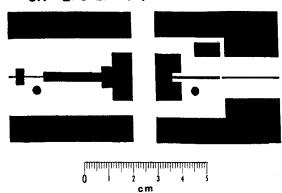
: .145 x .920 Z5 : .325 x .180 **Z**6 .730 x .315

Z7 : .710 x .425 with .140 x .150 Cutout : .035 x .780; C4 Tapped .36 from Center Z8

: 50Ω (.02 Wide)

C1, C4: Cold End Terminated Through Eyelet

3M EPSILANTO, .032 THK.,10Z.

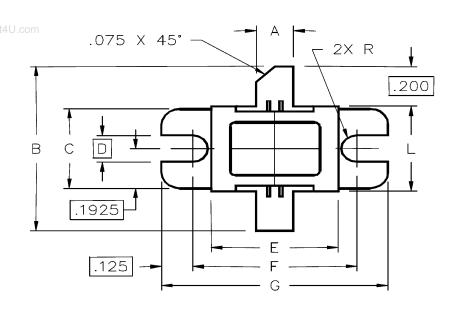


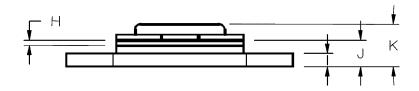


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PACKAGE MECHANICAL DATA

PACKAGE STYLE M112





	MINIMUM	MAXIMUM			MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM			INCHES/MM	INCHES/MM
Α	.145/3,68	.155/3,93		1	.055/1,40	.065/1,65
В	.750/19,05			\subset	.115/2,92	.135/3,43
С	.380/9,.65	.390/9,91		Κ		.230/5,64
D	.130,	/3,30		Г	.395/10,03	.410/10,41
E	.495/12,57	.505/12,83				
F	.640/16,26	.655/16,64				
G	.890/22,61	.910/23,11	П			
Н	.002/0,05	.006/0,15				